



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	1.9Ω @ $V_{GS} = -4.5V$	-530mA
	2.4Ω @ $V_{GS} = -2.5V$	-471mA
	3.4Ω @ $V_{GS} = -1.8V$	-397mA
	5.0Ω @ V _{GS} = -1.5V	-328mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low Package Profile
- 0.6mm x 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage: -1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

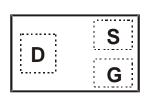
- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.001 grams (Approximate)

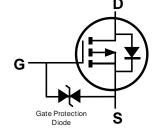
X2-DFN0604-3











Top View Package Pin Configuration

Equivalent Circuit

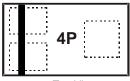
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP22D4UFO-7B	X2-DFN0604-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View Bar Denotes Gate and Source Side

4P = Product Type Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	-530 -383	mA
Pulsed Drain Current (Note 6)			I _{DM}	-0.6	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	P_{D}	820	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	155	°C/W
Total Power Dissipation (Note 6)	Steady State	P _D	390	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	317	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

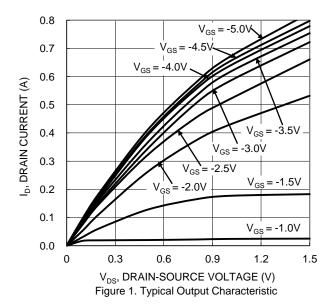
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -16V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		1	_	1.9		$V_{GS} = -4.5V$, $I_{D} = -100mA$	
Static Drain-Source On-Resistance	D-scars		_	2.4	Ω	$V_{GS} = -2.5V$, $I_{D} = -50mA$	
Static Drain-Source On-Nesistance	R _{DS(ON)}		_	3.4	32	$V_{GS} = -1.8V, I_D = -20mA$	
		_	_	5.0		$V_{GS} = -1.5V, I_{D} = -10mA$	
Diode Forward Voltage	V_{SD}	_	-0.6	-1.1	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	28.7	_	pF		
Output Capacitance	Coss	_	4.2	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_	2.9	_	pF	-1 - 1.0ivii iz	
Gate Resistance	Rg	_	399	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	0.4	_	nC	4.577.77	
Gate-Source Charge	Q _{gs}	_	0.08	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_{D} = -250\text{mA}$	
Gate-Drain Charge	Q_{gd}	_	0.06	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.8	_	ns	$V_{DD} = -15V$, $V_{GS} = -4.5V$, $R_{G} = 2\Omega$, $I_{D} = -200$ mA	
Turn-On Rise Time	t _R	_	5.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	31.1	_	ns		
Turn-Off Fall Time	t _F	_	16.4	_	ns		

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided 10µs pulse duty cycle = 1%
- 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.







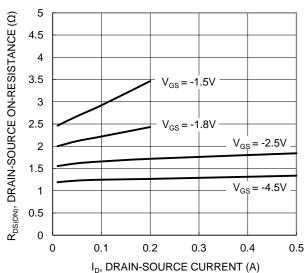


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

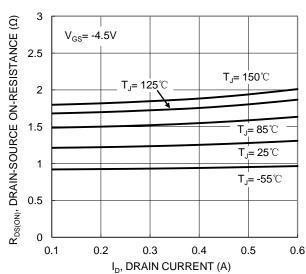


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

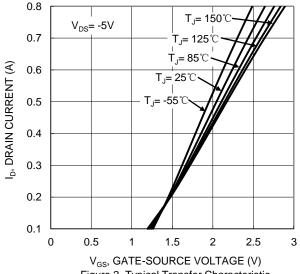
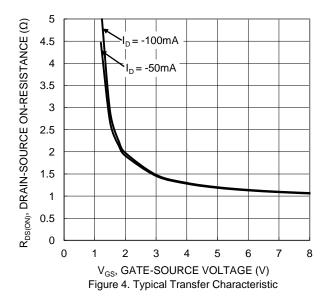


Figure 2. Typical Transfer Characteristic



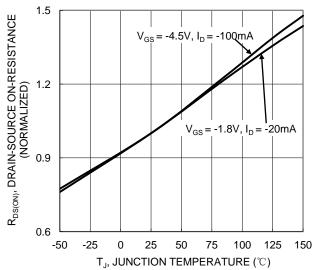


Figure 6. On-Resistance Variation with Temperature





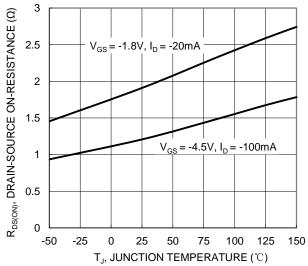
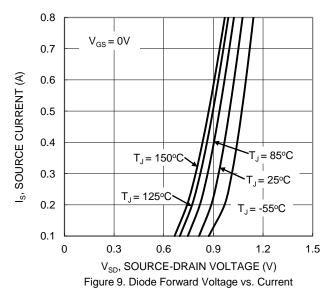


Figure 7. On-Resistance Variation with Temperature



8 7 6 5 $V_{GS}(V)$ 4 3 $V_{DS} = -10V, I_{D} = -250mA$ 2 1 0 0 0.1 0.2 0.3 0.4 0.5 0.6 0.7 Qg (nC)

Figure 11. Gate Charge

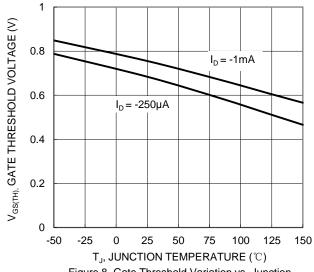
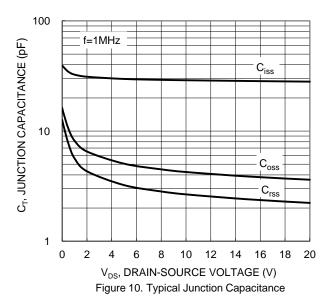


Figure 8. Gate Threshold Variation vs. Junction Temperature



 $\begin{array}{c} 1 \\ \hline R_{DS(ON)} \text{ Limited} \\ \hline 0.1 \\ \hline P_{W}=1\text{ms} \\ \hline P_{W}=10\text{ms} \\ \hline P_{W}=100\text{ms} \\ \hline P_{W}=150^{\circ}\text{C} \\ \hline P_{C}=25^{\circ}\text{C} \\ \hline P_{W}=10\text{ms} \\ \hline 0.01 \\ \hline 0.01 \\ \hline 0.1 \\ \hline 1 \\ \hline 10 \\ \hline 100 \\ \hline V_{DS}, DRAIN-SOURCE VOLTAGE (V) \\ \hline Figure 12, SOA, Seta Operation Area. \\ \hline \end{array}$

Figure 12. SOA, Safe Operation Area



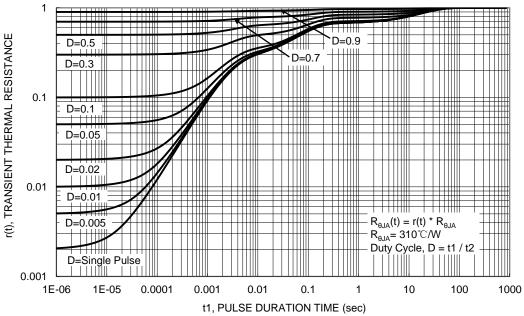


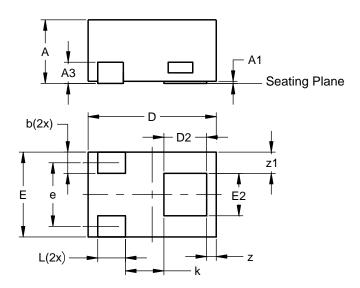
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3

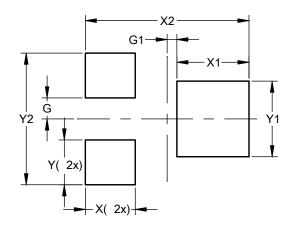


X2-DFN0604-3					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A1	0.00	0.03	0.02		
A3			0.10		
b	0.07	0.15	0.10		
D	0.55	0.65	0.60		
D2	0.15	0.25	0.20		
Е	0.35	0.45	0.40		
E2	0.15	0.25	0.20		
е	1		0.30		
k	0.15				
L	0.10	0.18	0.13		
Z	1		0.045		
z1	-		0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3



Dimensions	Value (in mm)
G	0.075
G1	0.035
Х	0.180
X1	0.260
X2	0.590
Υ	0.160
Y1	0.270
Y2	0.470



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